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DBs	USPAT, US-PGPUB, EPO, JPO, IBM, TDB			<input checked="" type="checkbox"/> Purge
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hanafi-hussein-t.in.
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hanafi-hussein-t.in.))) and silicide) and (flip$5 or turn$4)) and
flip$5
  
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	U	I	PT	P	Document ID	Issue Dat	Pages	Title	Current OR	Current *
1	□	□	□	□	US 20040036497	20040226	37	Semiconductor integrated circuit and its fabrication method	326/27	
2	□	□	□	□	US 20030215988	20031120	21	Self-aligned dual-gate transistor device and method of forming self-aligned dual-gate transistor device	438/157	257/E21.3;
3	□	□	□	□	US 20030117151	20030626	45	Semiconductor device and method of checking semiconductor storage device	324/658	
4	□	□	□	□	US 20020190323	20021219	15	Semiconductor device and its manufacturing method	257/351	257/350; 257/369;
5	□	□	□	□	US 20020160574	20021031	21	METHOD OF FORMING A DUAL-GATED SEMICONDUCTOR-ON-INSULATOR DEVICE	438/283	257/E21.3;
6	□	□	□	□	US 20020086465	20020704	13	Sub-lithographics opening for back contact or back gate	438/149	257/347; 257/352;
7	□	□	□	□	US 20020070760	20020613	37	Semiconductor integrated circuit and its fabrication method	326/121	257/E27.3;
8	□	□	□	□	US 20010009383	20010726	42	Semiconductor integrated circuit and its fabrication method	326/121	257/E27.3;
9	□	□	□	□	US 6636075 B2	20031021	36	Semiconductor integrated circuit and its fabrication method	326/102	257/E27.3;
10	□	□	□	□	US 6359472 B2	20020319	41	Semiconductor integrated circuit and its fabrication method	326/121	257/E27.3;
11	□	□	□	□	US 6194915 B1	20010227	36	Semiconductor integrated circuit device and process for manufacturing the same	326/121	257/E27.3;
12	□	□	□	□	US 6049110 A	20000411	51	Body driven SOI-MOS field effect transistor	257/347	257/280; 257/281;
13	□	□	□	□	US 5523598	19960604	47	Semiconductor integrated circuit device	257/301	257/390;